TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π–MOSV)

2SK2917

Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & Low\ drain-source\ ON\ resistance & : RDS\ (ON) = 0.21\ \Omega\ (typ.) \\ \bullet & High\ forward\ transfer\ admittance & : |Y_{fs}| = 17\ S\ (typ.) \\ \bullet & Low\ leakage\ current & : I_{DSS} = 100\ \mu A\ (max)\ (V_{DS} = 500\ V) \\ \end{array}$

• Enhancement mode : $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	500	V	
Drain-gate voltage (Ro	_{SS} = 20 kΩ)	V_{DGR}	500	V	
Gate-source voltage		V_{GSS}	±30	V	
Drain current	DC (Note 1)	I_{D}	18	А	
	Pulse (Note 1)	I_{DP}	72		
Drain power dissipation	n (Ta = 25°C)	P_{D}	90	W	
Single pulse avalanche	e energy (Note 2)	E _{AS}	915	mJ	
Avalanche current		I _{AR}	18	Α	
Repetitive avalanche e	nergy (Note 3)	E _{AR}	9	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature ra	ange	T _{stg}	-55~150	°C	

Unit: mm 15.8±0.5 Ø3.6±0.2 3.5 15.45±0.2 3.15-0.1 1. GATE 2. DRAIN 3. SOURCE JEDEC — JEITA — TOSHIBA 2-16F1B

Weight: 5.8 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.39	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	41.6	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 4.8 mH, R_{G} = 25 Ω , I_{AR} = 18 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.

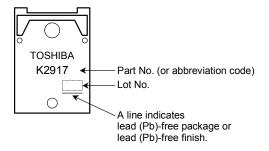
Electrical Characteristics (Ta = 25°C)

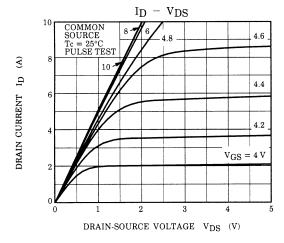
Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V	_	_	100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	500	_	_	V
Gate threshold v	oltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 10 A	_	0.21	0.27	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 10 A	10	17	_	S
Input capacitano	e	C _{iss}		_	3720	_	
Reverse transfe	r capacitance	C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	340	_	pF
Output capacitance		Coss] [_	1165	_	
Switching time	Rise time	t _r	$V_{GS} = 10.0 \text{ A}$ $V_{GS} = 10.0 \text{ A}$ $V_{OUT} = 10.0 \text{ A}$ $V_{OUT} = 200 \text{ V}$ $V_{DD} = 200 \text{ V}$	_	30	_	
	Turn-on time	t _{on}		l	70	l	ns
	Fall time	t _f		l	50	l	- IIS
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\rm W} = 10 \mu \rm s$	-	290	-	
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 18 A		80		
Gate-source charge		Q_{gs}		_	48	_	nC
Gate-drain ("miller") Charge		Q_{gd}		1	32	1	

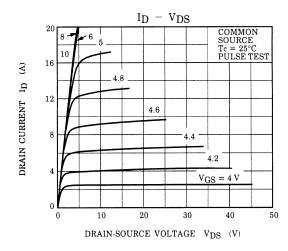
Source-Drain Ratings and Characteristics (Ta = 25°C)

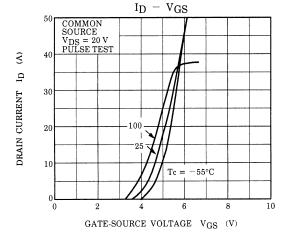
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_		_	18	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_		_	72	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 18 A, V _{GS} = 0 V	_	_	-2.0	V
Reverse recovery time	t _{rr}	I _{DR} = 18 A, V _{GS} = 0 V		540	_	ns
Reverse recovery charge	Q _{rr}	dl _{DR} / dt = 100 A / μs		5.4	-	μC

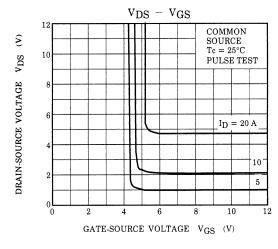
Marking

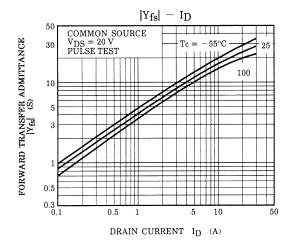


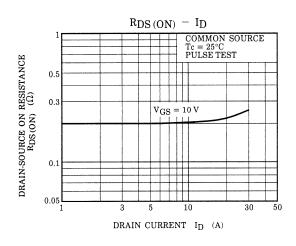


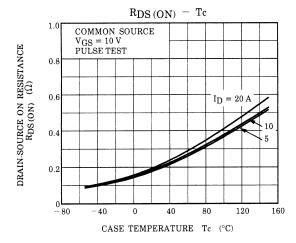


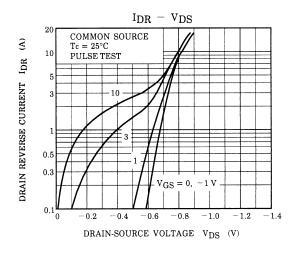


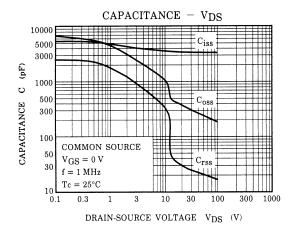


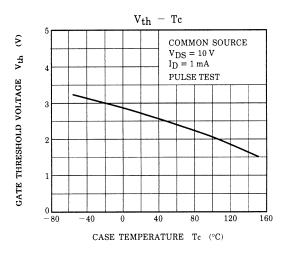


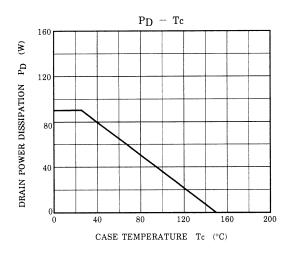


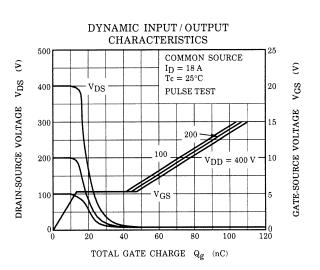


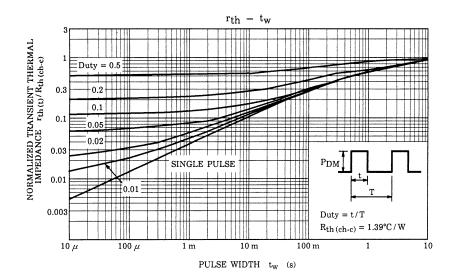


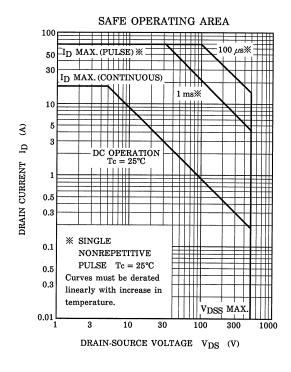


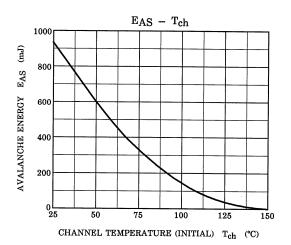


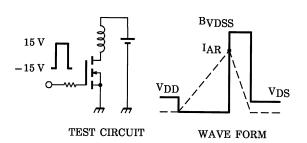












$$\begin{aligned} &RG = 25~\Omega \\ &V_{DD} = 90~V,~L = 4.8~mH \end{aligned} \qquad E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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